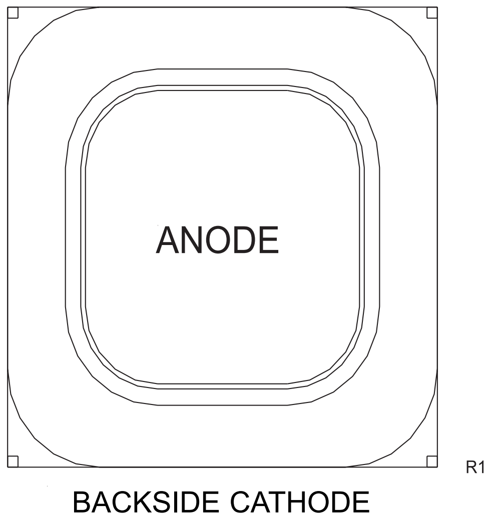
PROCESS CPD48
Schottky Diode
High Current Schottky Diode Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14 x 14 MILS
Die Thickness	9.0 MILS
Anode Bonding Pad Area	9.0 x 9.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER
62,250

PRINCIPAL DEVICE TYPES
CMPSH-3
CMPSH-3A
CMPSH-3C
CMPSH-3S

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R2 (1-August 2002)

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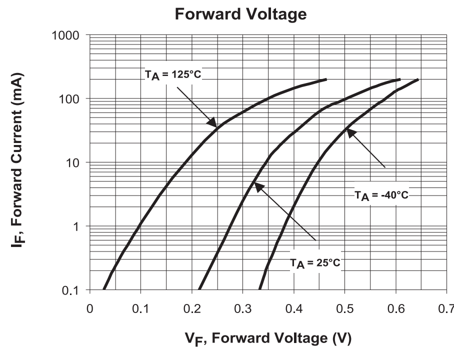
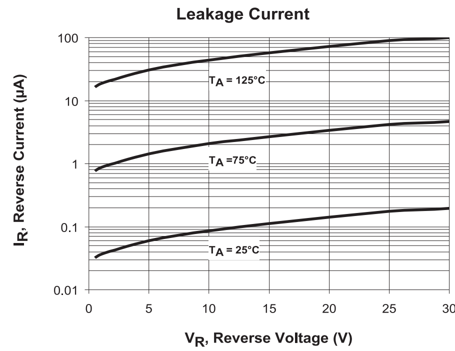
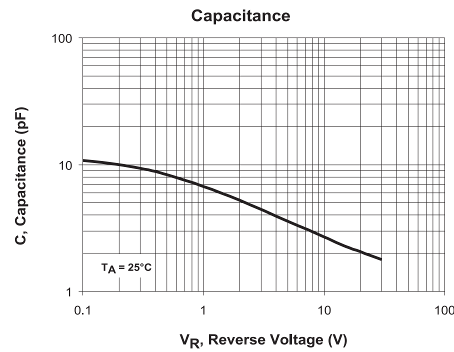
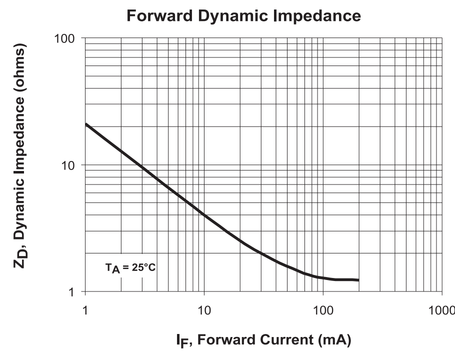
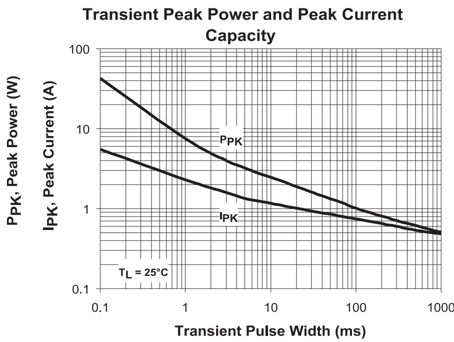
PROCESS CPD48
Typical Electrical Characteristics

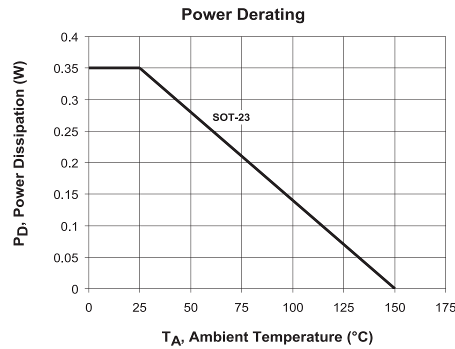












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